

## **AMENDMENT TO SPECIFICATION**

### **IN THE SPECIFICATION:**

A marked-up copy of the changes to selected paragraph(s) 0032 is provided below.  
Please enter these changes to the specification in the record.

Table 1, reproduced below, is representative of the advantages achieved by the aspects of the invention, compared to conventional methods. The ~~date~~ data in Table 1 and table 2 were generated using dual damascene wires and vias with 200nm minimum critical dimension. In Table 1, it is shown that a conventional method of fabrication yields approximately 15% non-defective devices (chips). In stark improvement, the use of the aspect of Figure 2 shows a yield of 60% of non-defective devices (chips). Of even greater yield is the aspect of the invention of Figures 3a through 3d which show a yield of 75% of non-defective devices (chips). The aspect of the invention of Figures 4a through 4d shows a yield of 90% of non-defective devices (chips). This improvement over the standard fabrication processes is attributable to the elimination of contaminants during the fabrication processes.